

IN THE SPECIFICATION:

Please amend the Specification as follows:

On Page 2, please revise the amended second complete paragraph on this page, and please rewrite by replacing with the following paragraph:

--The invention relates to a semiconductor wafer comprising a substrate wafer made of monocrystalline silicon and an epitaxial layer deposited thereon, which is characterized in that the substrate wafer has a resistivity of from 0.1 to 50 Ωcm , an oxygen concentration of less than $7.5 \times 10^{17} \text{ atcm}^{-3}$, and a nitrogen concentration of from 1×10^{13} to $5 \times 10^{15} \text{ atcm}^{-3}$, and the epitaxial layer has a thickness of from 0.2 to 1.0 μm and has a top surface on which fewer than 30 LLS defects with a size of more than 0.085 μm can be detected.--